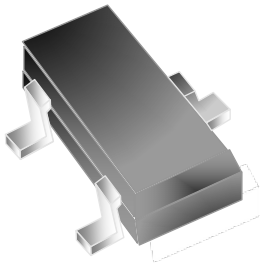
WM01P41M

P-Channel Enhancement MOSFET

Features

- Way-on Small Signal MOSFETs
- V_{DS}= -12V, I_D = -4.1A
  $R_{DS(on)}$ < 45mΩ @ V_{GS} = -4.5V
  $R_{DS(on)}$ < 60mΩ @ V_{GS} = -2.5V
- Trench LV MOSFET Technology

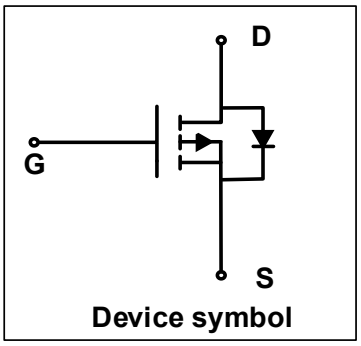


SOT-23

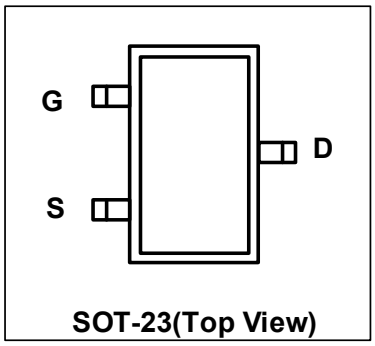
Mechanical Characteristics

- SOT-23 Package
- Marking : Making Code
- RoHS Compliant

Schematic & PIN Configuration



Device symbol



SOT-23(Top View)

Absolute Maximum Rating (T_A=25°C unless otherwise noted)

Rating		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-12	V
Gate-Source Voltage		V_{GS}	±8	V
Continuous Drain Current	T_A=25°C	I_D	-4.1	A
Pulsed Drain Current[1]		I_{DM}	-15	A
Power Dissipation	T_A=25°C	P_D	1.2	W
Junction and Storage Temperature Range		T_J ,T_{STG}	-55 to 150	°C

Thermal Characteristics

Rating	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient[2]	$R_{\theta JA}$	104	°C /W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}= 0V, I_D= -250μA	-12	-	-	V
Gate-body Leakage Current	I_{GSS}	V_{DS}= 0V, V_{GS}= ±8V	-	-	±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}= -12V, V_{GS}= 0V	-	-	-1	μA
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS} = V_{DS}, I_D = -250 μA	-0.5	-0.7	-0.9	V
Drain Source on-Resistance[3]	$R_{DS(on)}$	V_{GS}= -4.5V, I_D= -3.5A	-	30	45	mΩ
		V_{GS}= -2.5V, I_D= -3.0A	-	40	60	
		V_{GS}= -1.8V, I_D= -2.0A	-	60	90	
Dynamic Characteristics[4]						
Input Capacitance	C_{iss}	V_{GS}= 0V, V_{DS} = -6V, f = 1MHz	-	1250	-	pF
Output Capacitance	C_{oss}		-	330	-	
Reverse Transfer Capacitance	C_{rss}		-	300	-	
Switching Characteristics[4]						
Total Gate Charge	Q_g	V_{GS}= -4.5V, V_{DS}= -4V, I_D= -3.5A	-	4.4	-	nC
Gate−Source Charge	Q_{gs}		-	1.3	-	
Gate−Drain Charge	Q_{gd}		-	1.5	-	
Turn−On Delay Time	$t_{d(on)}$	V_{GS}= -4.5V ,V_{DD}= -4V, R_g = 3Ω, I_D = -3.5A	-	11.2	-	ns
Rise Time	t_r		-	32.5	-	
Turn−Off Delay Time	$t_{d(off)}$		-	30	-	
Fall Time	t_f		-	9.5	-	
Drain-Source Diode Characteristics						
Body Diode Voltage[3]	V_{SD}	V_{GS}=0V, I_S= -1A	-	-	-1.2	V
Continuous Source Current	I_S		-	-	-4.1	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C.

2. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.

3. Pulse Test: Pulse width≤300μs, duty cycle≤2%.

4. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

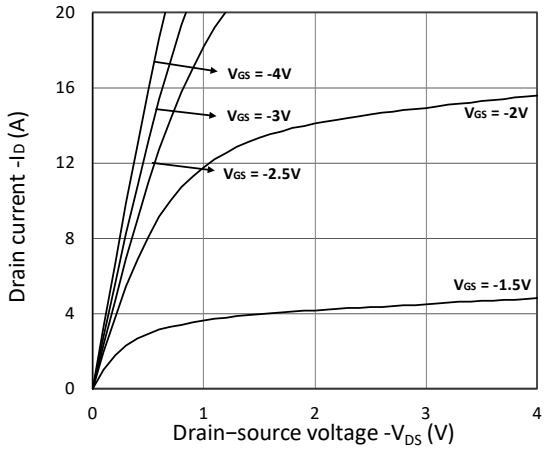


Figure 1. Output Characteristics

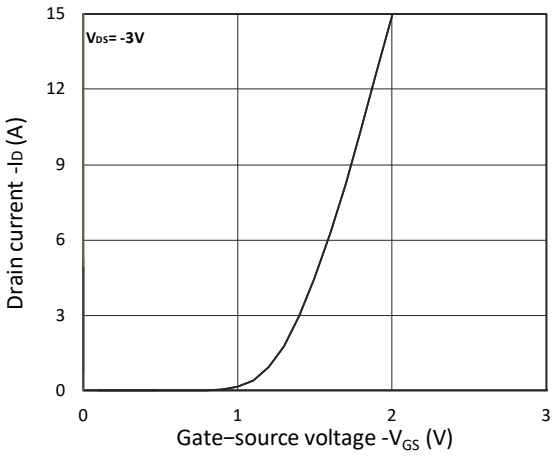


Figure 2. Transfer Characteristics

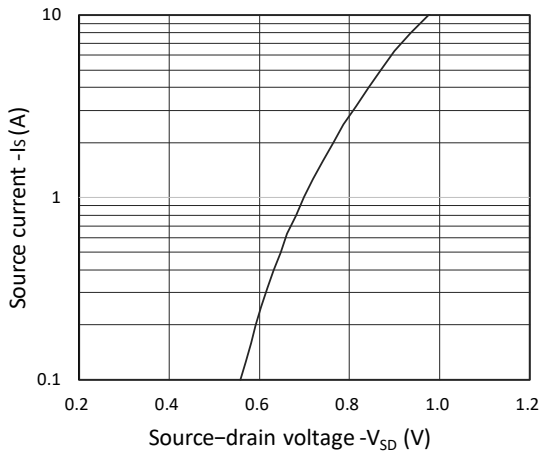


Figure 3. Forward Characteristics of Reverse

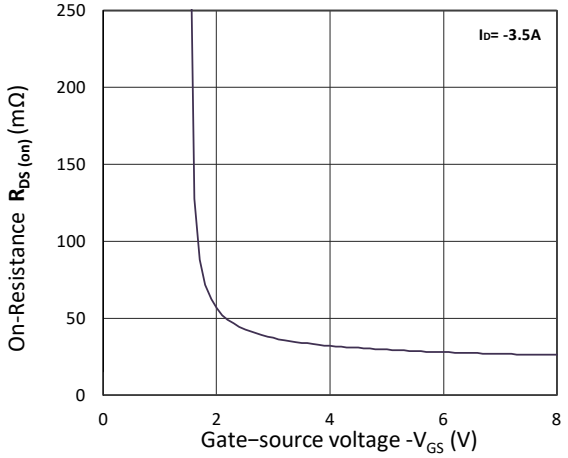


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

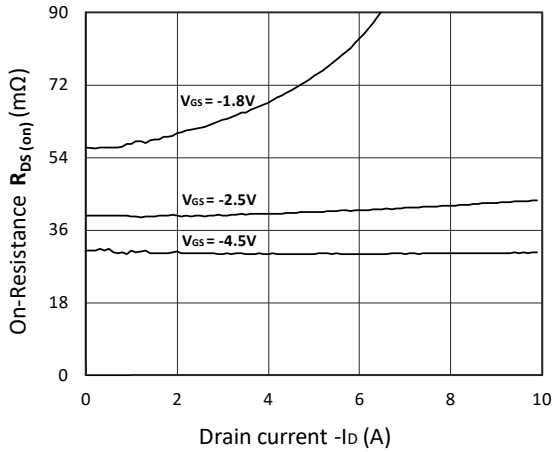


Figure 5. $R_{DS(ON)}$ vs. I_D

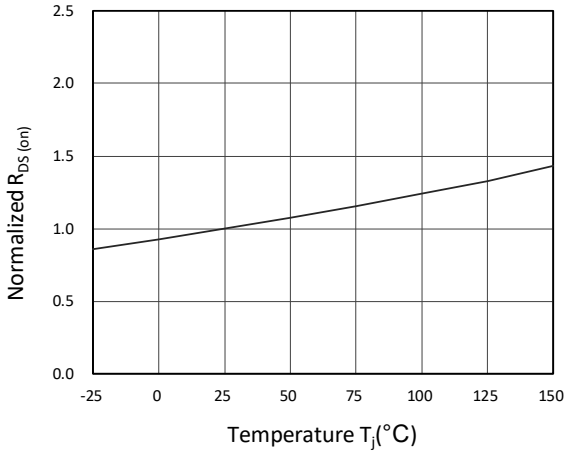


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

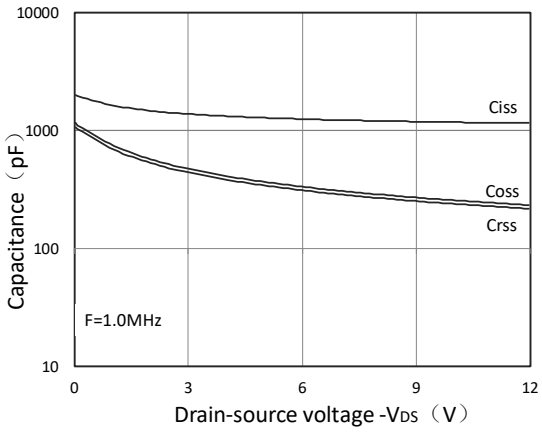


Figure 7. Capacitance Characteristics

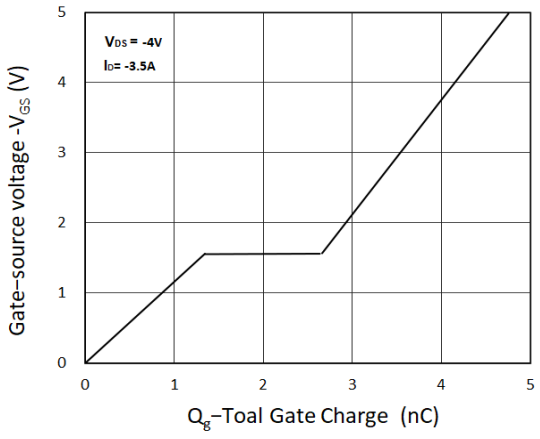
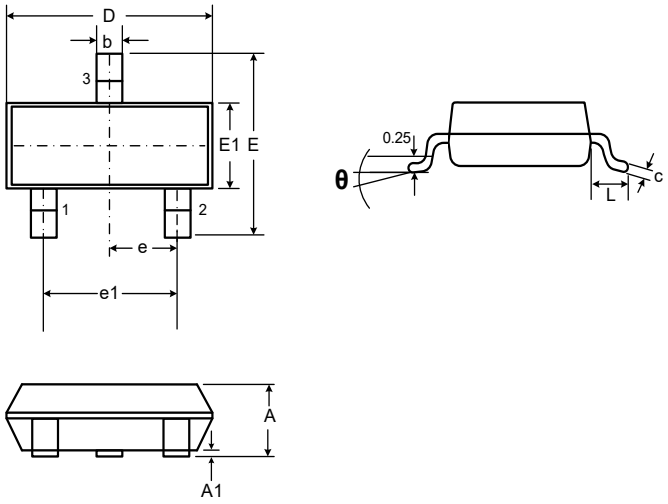
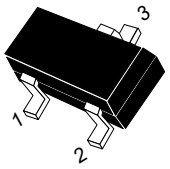


Figure 8. Gate Charge Characteristics

Outline Drawing – SOT-23

PACKAGE OUTLINE

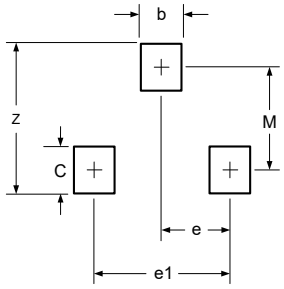




SOT-23

DIMENSIONS

SYMBOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.15	0.035	0.045
A1	0.00	0.10	0.000	0.004
b	0.30	0.50	0.012	0.020
c	0.08	0.15	0.003	0.006
D	2.80	3.00	0.110	0.118
E	2.25	2.55	0.089	0.100
E1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.037 BSC	
e1	1.80	2.00	0.071	0.079
L	0.55REF		0.022REF	
θ	0°	8°	0°	8°



DIMENSIONS		
DIM	**INCHES**	**MILLIMETERS**
M	**0.080**	**2.02**
C	**0.032**	**0.80**
Z	**0.111**	**2.82**
e	**0.037 BSC**	**0.95 BSC**
e1	**0.075 BSC**	**1.90 BSC**
b	**0.032**	**0.80**

Notes

1. Dimensioning and tolerances per ANSI Y14.5M, 1985.

2. Controlling Dimension: Inches

3. Pin 3 is the cathode (Unidirectional Only).

4. Dimensions are exclusive of mold flash and metal burrs.

Marking Codes

Part Number	WM01P41M
Marking Code	**S5**

Package Information

Qty：3k/Reel

CONTACT INFORMATION

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